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This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of claims:**

1. (Currently Amended) A method for fabricating metal wirings, comprising the steps of:
  - forming a ground resin film by applying a resin onto an insulating substrate;
  - patterning the ground resin film; and
  - forming a low-resistance metal film over the patterned ground resin film by a wet film formation technique such that wherein the patterned ground resin film is enclosed by the low-resistance metal film and the insulating substrate encloses the patterned ground resin film, wherin the low-resistance metal film is a single layer film containing any one of Cu, Ni, Sn, Au, Ag, Cr, or Pd or the low-resistance metal film is a multilayer film containing at least one single layer film containing Cu, Ni, or Au.
2. (Original) A method according to Claim 1, wherein the ground resin film is made of a photosensitive resin that can be patterned by exposure and development.
3. Cancelled.
4. (Original) A method according to Claim 1, wherein the ground resin film is made of polyimide.
5. (Original) A method according to Claim 1, wherin plating is used as the wet film formation technique, and the ground resin contains a plating catalyst.
6. (Original) A method according to Claim 1, further comprising:
  - a step for, before the step of forming the low-resistance metal film, modifying a surface of the ground resin film.

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7. (Original) A method according to Claim 6, further comprising:  
a set for, after the step of modifying the surface of the patterned ground resin film,  
forming on the surface-modified ground resin film a metal layer serving as a catalyst in the  
process of forming the low-resistance metal film by the wet film formation technique.
8. (Original) A method according to Claim 7, wherein the step of forming the  
metal layer acting as a catalyst in the process of forming the low-resistance metal film by the wet  
film formation technique comprises the steps of:  
making metal ions adsorbed onto the surface-modified ground resin film; and  
reducing the metal ions.
9. (Original) A method according to Claim 6, wherein the ground resin film is  
made of a photosensitive resin which can be patterned by exposure and development.
10. Cancelled.
11. (Original) A method according to Claim 6, wherein the ground resin film is  
made of polyimide.
12. (Original) The metal wiring fabricating method according to claim 11,  
wherein the step of modifying the surface of the patterned ground resin film is a process using  
KOH.
13. (Original) A method according to Claim 8, wherein  
the metal ions to be adsorbed onto the surface-modified ground resin are any one of Cu,  
Ag and Pd ions.
14. (Original) A method according to Claim 8, wherein  
the step of reducing the metal ions is a process in which ultraviolet rays are irradiated to  
places where the low-resistance metal film is to be formed, by which the metal ions are  
selectively reduced.

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15. (Previously Presented) The method according to claim 1, wherein the ground resin film has a thickness of between 0.05  $\mu\text{m}$  and 0.5 $\mu\text{m}$ .

16. (New) The method according to claim 1, wherein a planform of the patterned ground resin film and a planform of the low-resistance metal film are similar with each other.